TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2 S C 5 2 0 1

HIGH VOLTAGE SWITCHING APPLICATIONS

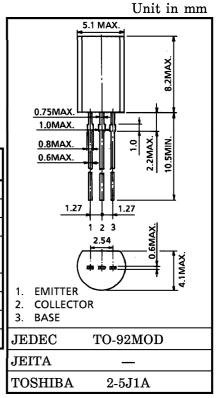
• High Voltage : $V_{CEO} = 600 \text{ V}$

• Low Saturation Voltage

: $V_{CE (sat)} = 1.0 \, V (Max.) (I_{C} = 20 \, mA, \, I_{B} = 0.5 \, mA)$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage		v_{CBO}	600	V	
Collector-Emitter Voltage		v_{CEO}	600	V	
Emitter-Base Voltage		v_{EBO}	7	V	
Collector Current	DC	$I_{\mathbf{C}}$	50	mA	
	Pulse	I_{CP}	100		
Base Current		$I_{\mathbf{B}}$	25	mA	
Collector Power Dissipation		PC	900	mW	
Junction Temperature		T_{j}	150	°C	
Storage Temperature Range		$\mathrm{T_{stg}}$	-55~150	°C	



Weight: 0.36 g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 600 \text{ V}, I_{E} = 0$	_	_	1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 7 V, I_{C} = 0$	_	_	1	μ A
Collector-Emitter Breakdown Voltage	V _{CEO}	$I_{\mathrm{C}}=1\mathrm{mA},~I_{\mathrm{B}}=0$	600	_	_	v
DC Current Gain	h _{FE (1)}	$V_{ ext{CE}} = 5 \text{ V}, \text{ I}_{ ext{C}} = 1 \text{ mA}$	80	_	_	
	hFE (2)	$V_{CE} = 5 V$, $I_{C} = 20 mA$	100	_	300	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{\mathrm{C}}=20\mathrm{mA},~I_{\mathrm{B}}=0.5\mathrm{mA}$	_	_	1.0	V
Base-Emitter Voltage	$v_{ m BE}$	$V_{CE} = 5 \text{ V}, I_{C} = 20 \text{ mA}$	_	0.66	0.85	V
Collector Output Capacitance	C_{ob}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	6.5	_	pF

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